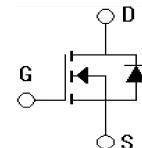
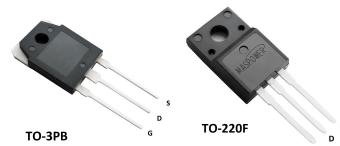


Features

- Low On-Resistance
- Fast switching
- High Input Resistance
- RoHS Compliant



Applications

- Electronic ballasts
- Electronic Transformer
- Switch Mode Power Supply

Absolute Ratings ($T_c=25^\circ C$)

Parameter	Symbol	Value		Unit
Drain-Source Voltage	V_{DSS}	500		V
Drain Current -continuous T=25°C	I_D	20*		A
		15		A
Drain Current - pulse (note 1)	I_{DM}	80		A
Gate-Source Voltage	V_{GSS}	± 30		V
Single Pulsed Avalanche Energy (note 2)	E_{AS}	1000		mJ
Power Dissipation (TO-3PB\TO-247\TO-220)	PD	290		W
	TC=25°C	2.17		W/°C
Power Dissipation(TO-220F)	PD	31.7		W
	TC=25°C	0.25		W/°C
Storage Temperature	T_{STG}	-55~+150		°C
Junction Temperature	T_j	150		°C

*Drain current limited by maximum junction temperature

Electrical Characteristics($T_{CASE}=25^\circ C$ unless otherwise specified)

Parameter	Symbol	Tests conditions	Min	Type	Max	Units
Off-Characteristics						
Drain-Source Voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	500	-	-	V
Breakdown Voltage Temperature Coefficient	ΔBV_{DSS} $/\Delta T_J$	$I_D=250\mu A$, referenced to 25°C	-	0.6	-	V/°C

Drain cut-off current	I_{DSS}	$V_{DS}=500V, V_{GS}=0V$	-	-	1	μA
		$V_{DS}=400V, T_j=125^\circ C$	-	-	10	
Gate-body leakage current,forward	I_{GSSF}	$V_{DS}=0V, V_{GS}=30V$	-	-	100	nA
Gate-body leakage current,reverse	I_{GSSR}	$V_{DS}=0V, V_{GS}=-30V$	-	-	-100	nA
On-Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	-	4.0	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=12A$ (note 3)	-	0.2	0.25	Ω
Forward Transconductance	g_{fs}	$V_{DS}=40V, I_D=9.5A$ (note 3)	-	19.7	-	S
Dynamic Characteristics						
Input capacitance	C_{iss}	$V_{DS}=25V,$ $V_{GS}=0V,$ $f=1.0MHz$	-	2850	3900	pF
Output capacitance	C_{oss}		-	260	355	
Reverse transfer capacitance	C_{rss}		-	7	23	
Switching Characteristics						
Turn-On delay time	$t_{d(on)}$	$V_{DD}=250V, I_D=20A,$ $R_G=25\Omega,$ $V_{GS}=10V$ (note 4,5)	-	30	92	ns
Turn-On rise time	t_r		-	43	170	ns
Turn-Off delay time	$t_{d(off)}$		-	110	265	ns
Turn-Off Fall time	t_f		-	50	122	ns
Total Gate Charge	Q_g	$V_{DS}=400V,$ $I_D=20A,$ $V_{GS}=10V$ (note4,5)	-	48.7	59.3	nC
Gate-Source charge	Q_{gs}		-	9.5	-	nC
Gate-Drain charge	Q_{gd}		-	20.6	-	nC
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=20A$ (note 3)	-	-	1.4	V
Maximum Continuous Drain-Source Diode Forward Current		I_S	-	-	20	A
Reverse recovery time	t_{rr}	$V_{GS}=0V, I_F=20A$ $dI/dt=100A/us$ (note 3)	-	400	-	ns
Reverse recovery charge	Q_{rr}		-	4.2	-	μC

Thermal Characteristic

Parameter	Symbol	Value		Unit
		MS20N50FB \FC\FT	MS20N50FS	
Thermal Resistance, Junction-to-Case	R _{θJC}	0.43	3.94	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	40	80	°C/W

Order Message

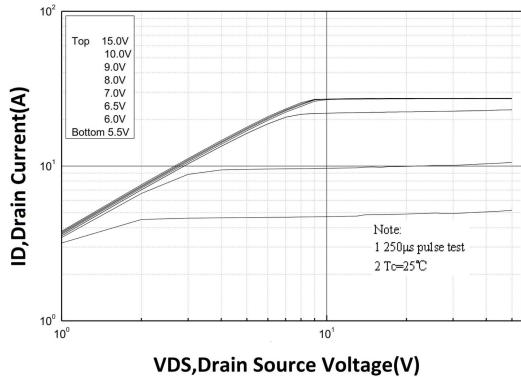
Order codes	Package	Packaging
MS20N50FB	TO-3PB	Tube
MS20N50FC	TO-247	Tube
MS20N50FS	TO-220F	Tube
MS20N50FT	TO-220	Tube

Notes:

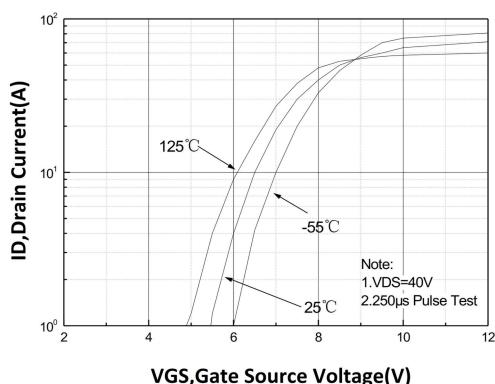
1. Repetitive rating: Pulse width limited by maximum junction temperature
2. Starting T_j=25°C, V_{DD}=50V, L=5mH, R=25Ω, I_{AS}=24.0A
3. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%

Electrical Characteristics

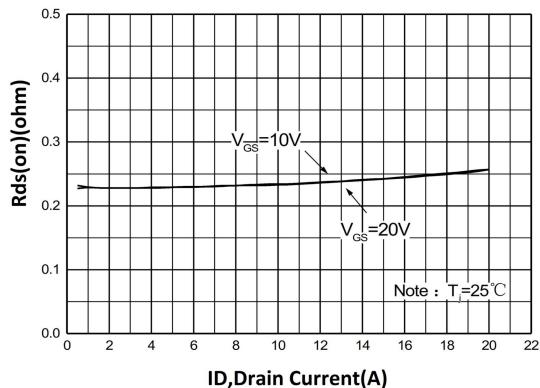
On-Region Characteristics



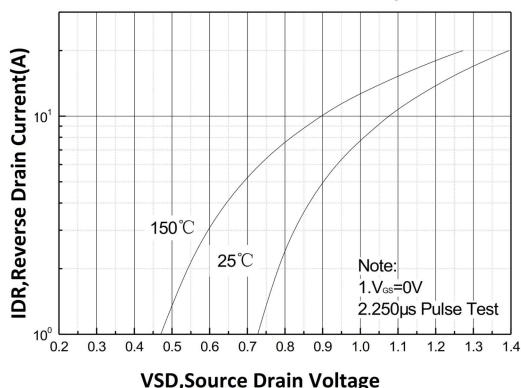
Transfer Characteristics



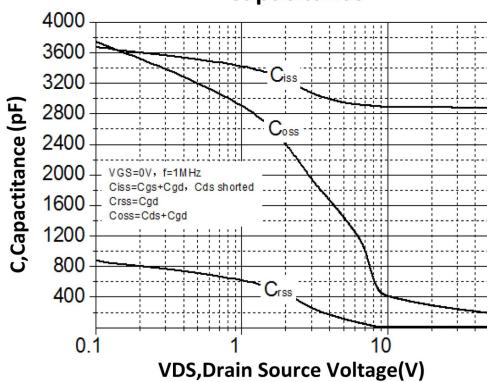
**On-Resistance Variation vs
Drain Current and Gate Voltage**



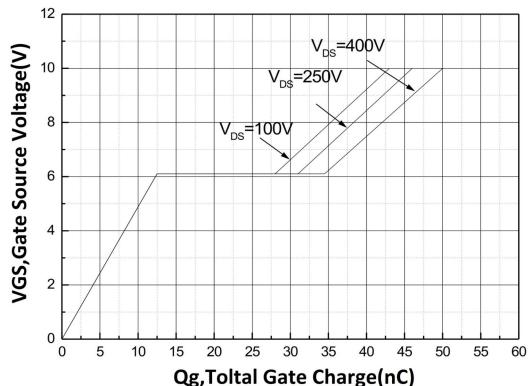
**Body Diode Forward Voltage Variation
vs. Source Current and Temperature**

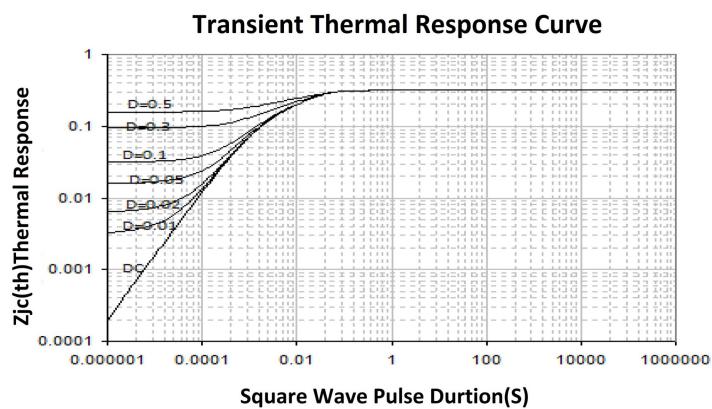
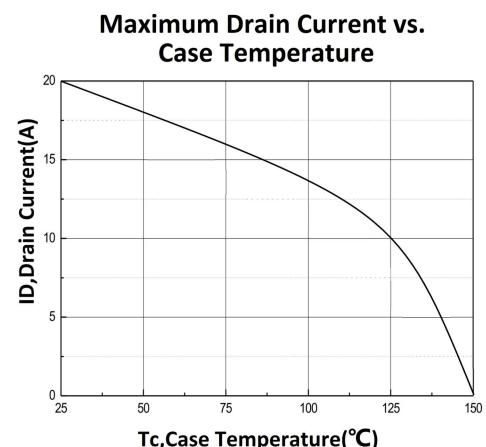
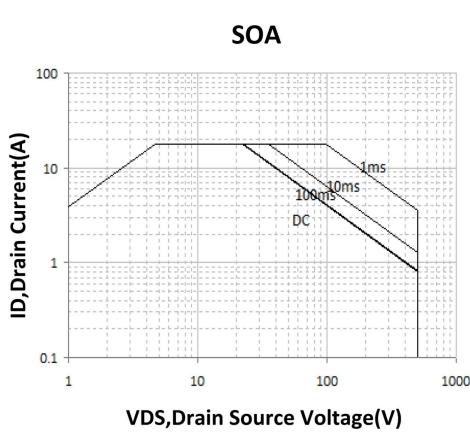
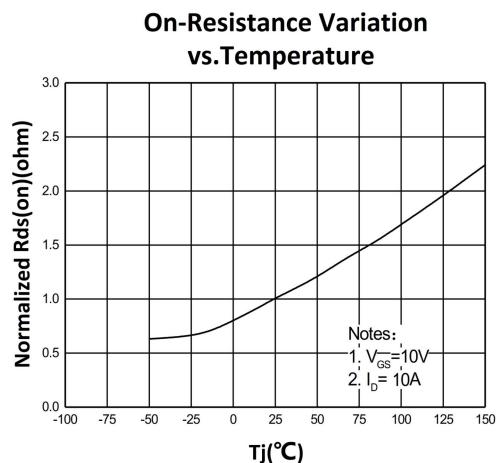
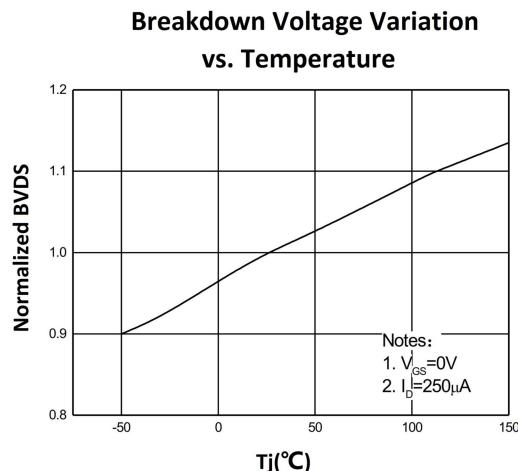


Capacitance

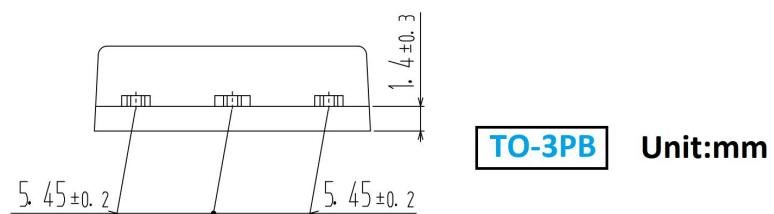
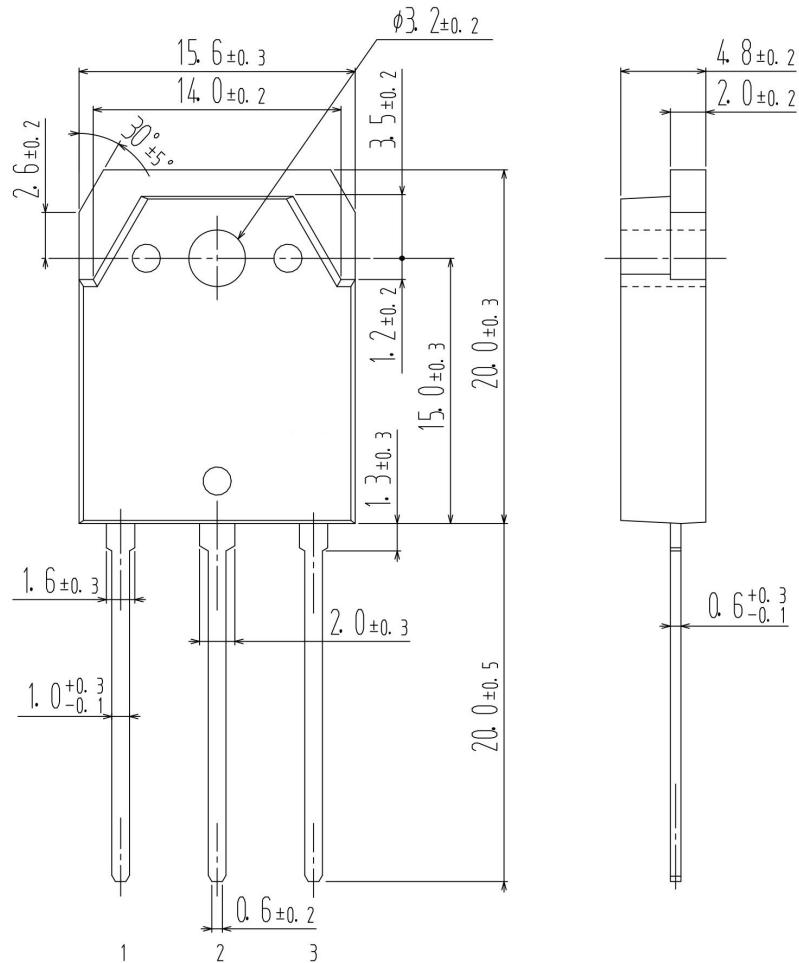


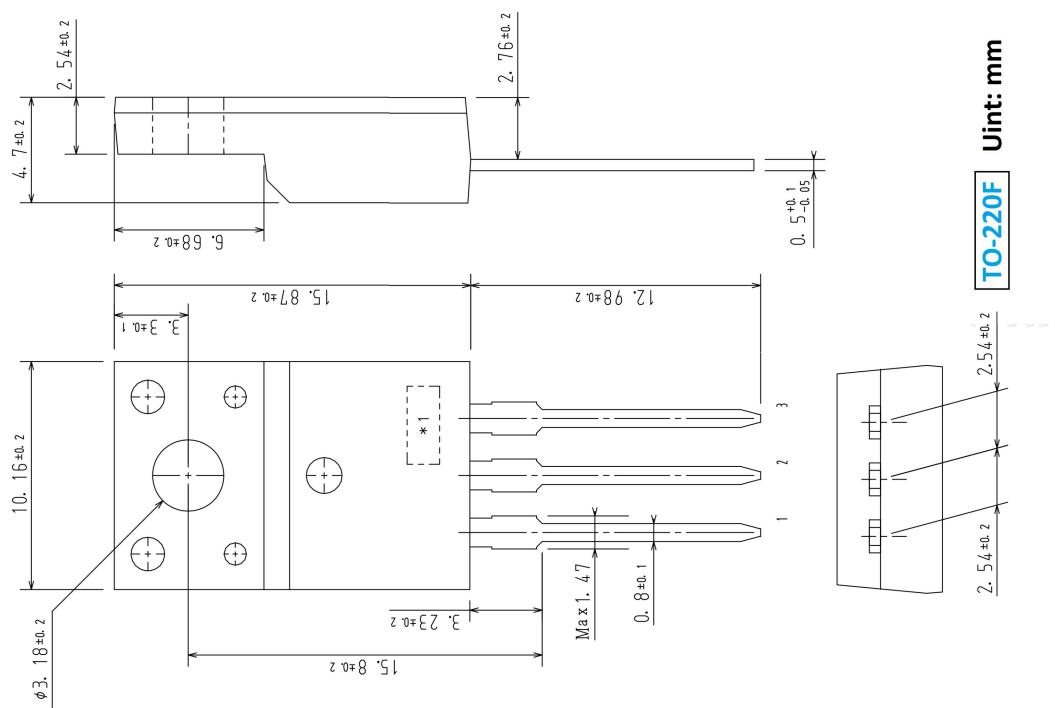
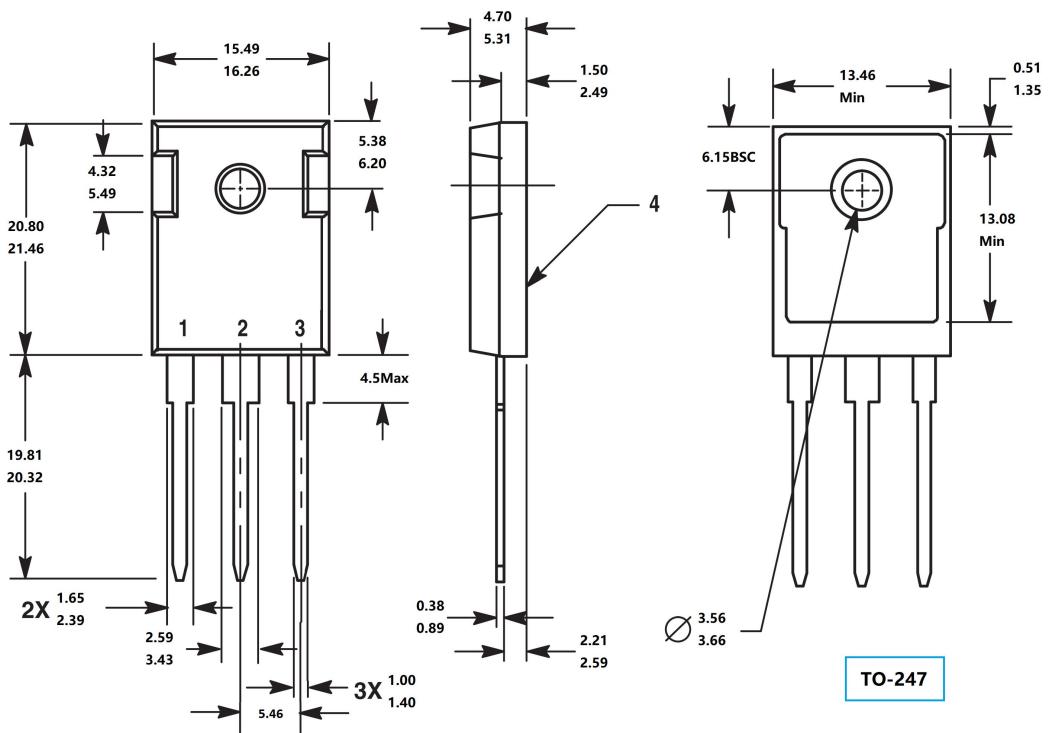
Gate Charge Characteristics

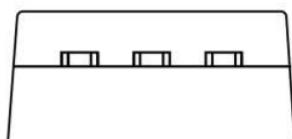
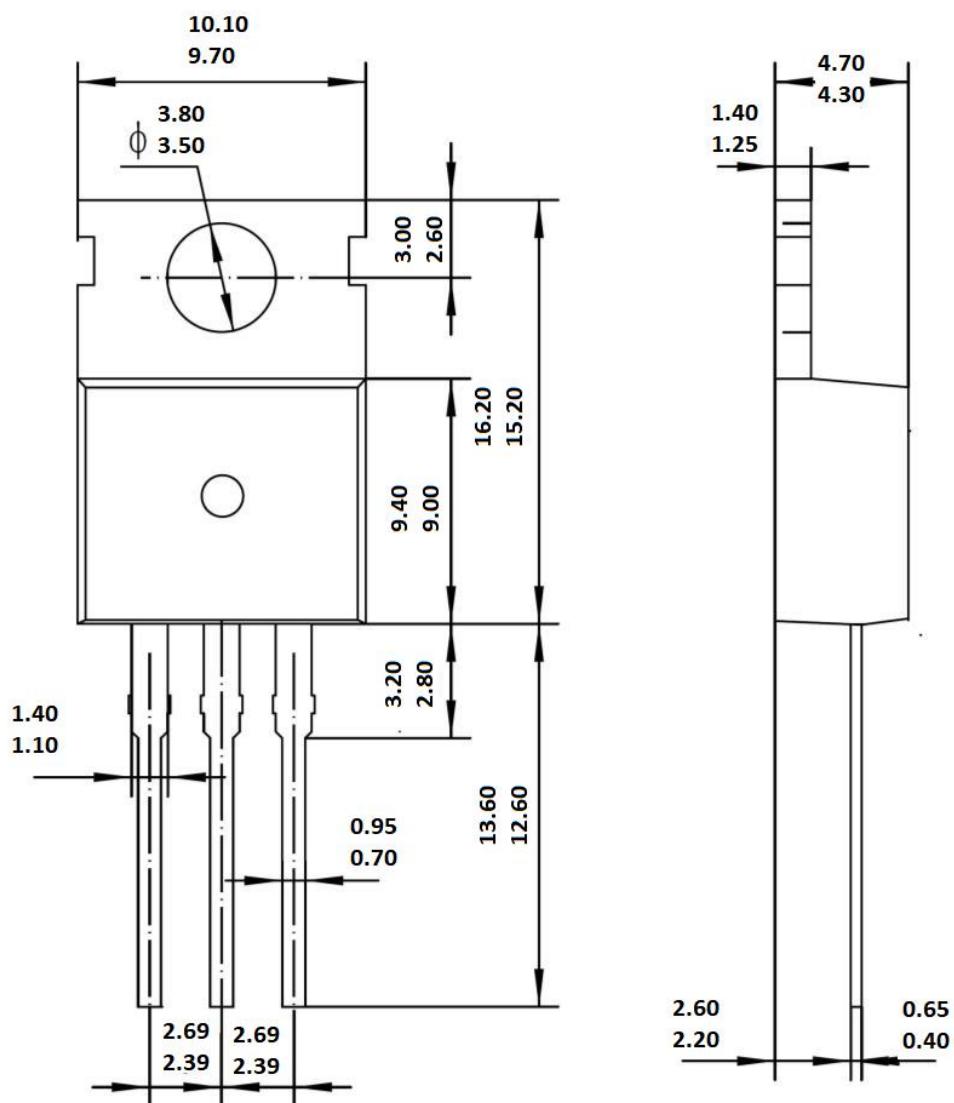




Package Mechanical DATA







TO-220

Unit: mm